IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Takamitsu HIGUCHI et al.

Application No.: New US Application

Filed: August 21, 2003 Docket No.: 116916

For: SUBSTRATE FOR ELECTRONIC DEVICES, MANUFACTURING METHOD

THEREFOR, AND ELECTRONIC DEVICE

<u>INFORMATION DISCLOSURE STATEMENT</u>

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the reference(s) listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the reference(s) be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- 2. The present application was filed or entered the U.S. National Stage of the PCT after June 30, 2003. In accordance with the June 11, 2003, Notice waiving the requirements of 37 C.F.R. §1.98(a)(2)(i), copies of any U.S. patents and patent application publications are not attached.
- 3. English-language Abstracts of the non-English language references are attached hereto.
- 4. Computer-generated English translations of the following Japanese Patent Publications have been obtained from the website of the Japanese Patent Office ([http://www.jpo.go.jp]), and are attached, but have not been reviewed for accuracy. See References 13-27.
- 5. Relevance of the non-English language references Nos. 26 and 28-30 are discussed in the present specification.

Respectfully submitted,

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JAO:JSA/tmw

Date: August 21, 2003

OLIFF & BERRIDGE, PLC P.O. Box 19928 Alexandria, Virginia 22320 Telephone: (703) 836-6400 DEPOSIT ACCOUNT USE
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Form PTO-1449 (REV. 8-83)	US Dept. of Commerce PATENT & TRADEMARK OFFICE			ATTY DOCKET NO. 116916			APPLICATION NO. New US Application		
INFO	RMATI	ON DISCLOSURE STATEMENT							
(Use several sheets if necessary)			APPLICANTS Takamitsu HIGUCHI et al.						
			FILING I August 2						
		U.S.	PATE	ENT DOCU	MENTS				
EXAMINER INITIAL		DOCUMENT NUMBER		DATE NAME			CLASS	SUB CLASS	
	1	6,232,242 B1	05/1	15/2001	Hata et al.				
	2	5,155,658	10/1	3/1992	Inam et al.				
	3	5,173,474	12/2	22/1992	Connell et al.				
	4	5,270,298	12/1	4/1993	Ramesh			-	
	5	5,358,925	10/2	25/1994	Neville Connell et al.				
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	12	6,121,647	09/1	9/2000	Yano et al.	***			
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	13	JP A 2000-332569 (with abstract and translation)	11/3	0/2000	Japan				
	14	JP A 2001-077102 (with abstract and translation)	03/2	3/2001	Japan				
	15	JP A 6-097452 (with abstract and translation)	04/0	8/1994	Japan				
	16	JP A 8-109099 (with abstract and translation)	04/3	0/1996	Japan				
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	18	JP A 8-264524 (with abstract and translation)	10/1	1/1996	Japan			<u>.</u>	
	19	JP A 9-110592 (with abstract and translation)	04/2	8/1997	Japan				
	20	JP A 10-017394 (with abstract and translation)	01/20	0/1998	Japan	·			
EXAMINER					DATE	CONSIDE	ERED		
Examiner: In	itial if onforma	citation considered, whether or not citance and not considered. Include copy of	ation f this f	is in confe	ormance with M.P.E.P. 609; dra- next communication to applicant.	w line thi	ough citatio	n if not in	

Date: August 21, 2003

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	21	JP A 9-263494 (with abstract and translation)	10/07/1997	Japan					
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	26	JP A 2001-122698 (with abstract and translation)	05/08/2001	Japan	100 P 40 P 100 P				
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	28	Fork et al., "Epitaxial yttria-stabilized zirconia on hydrogen-terminated Si by pulsed laser deposition", Appl. Phys. Letter 57, September 10, 1990, pp 1137-1139							
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	30	Hou et al., "Structure and properties of epitaxial Ba _{0.5} Sr _{0.5} TiO ₃ /SrRuO ₃ /ZrO ₂ heterostructure on Si grown by off-axis sputtering", Appl. Phys. Lett. 67, September 4, 1005, pp 1387-1389							
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